

Title (en)

METHOD FOR PRODUCING CMOS TRANSISTORS AND RELATED DEVICES

Title (de)

HERSTELLUNGSVERFAHREN VON CMOS-TRANSISTOREN UND DERARTIGE BAUELEMENTE

Title (fr)

PROCEDE DE REALISATION DE TRANSISTORS CMOS ET DISPOSITIFS ASSOCIES

Publication

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Application

EP 99958336 A 19991215

Priority

- FR 9903151 W 19991215
- FR 9816028 A 19981218

Abstract (en)

[origin: FR2787634A1] Engraving process comprises etching an active layer or rendering zones of the layer inactive to leave active islands for making sources (12), channels (10) and drains of N-type and P-type transistors. The active islands are covered by an insulating layer (8) e.g. of silicium oxide, covered in turn by a conducting layer (9) of N+ doped polycrystalline silicium, tungsten, molybdenum or aluminum, etched with the transistor grids. The procedure can employ a substrate (4) or glass, plastic or quartz.

IPC 1-7

H01L 21/84; **H01L 27/12**

IPC 8 full level

G02F 1/1368 (2006.01); **G09F 9/30** (2006.01); **G09F 9/35** (2006.01); **H01L 21/336** (2006.01); **H01L 21/77** (2006.01); **H01L 21/8238** (2006.01); **H01L 21/84** (2006.01); **H01L 27/08** (2006.01); **H01L 27/092** (2006.01); **H01L 27/12** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP KR US)

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